



TO-92S Plastic-Encapsulate Transistors

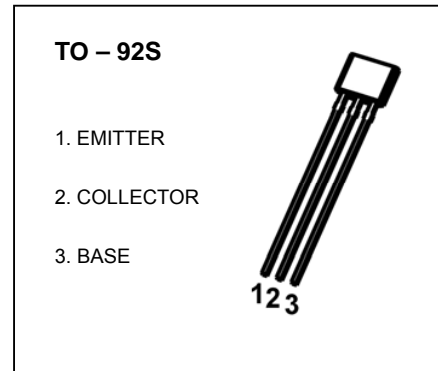
KTA1297 TRANSISTOR (PNP)

FEATURES

- General Purpose Switching Application

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-20	V
V _{CEO}	Collector-Emitter Voltage	-20	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current	-2	A
P _C	Collector Power Dissipation	400	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	312	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.1mA, I _E =0	-20			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.1mA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-20V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-2V, I _C =-0.1A	120		400	
	h _{FE(2)}	V _{CE} =-2V, I _C =-2A	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A, I _B =-0.1A			-0.5	V
Base-emitter voltage	V _{BE}	V _{CE} =-2V, I _C =-0.1A			-0.85	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		40		pF
Transition frequency	f _T	V _{CE} =-2V, I _C =-0.5A		120		MHz

CLASSIFICATION OF h_{FE(1)}

RANK	Y	GR
RANGE	120-240	200-400